

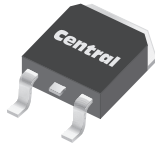
CJD200 NPN  
CJD210 PNP

**SURFACE MOUNT SILICON  
COMPLEMENTARY  
POWER TRANSISTORS**



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**DPAK**  
**POWER!**



**DPAK CASE**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CJD200 and CJD210 are complementary silicon power transistors manufactured in a surface mount package designed for high current amplifier applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter-Base Voltage	$V_{EBO}$	8.0	V
Continuous Collector Current	$I_C$	5.0	A
Peak Collector Current	$I_{CM}$	10	A
Continuous Base Current	$I_B$	1.0	A
Power Dissipation	$P_D$	12.5	W
Power Dissipation ( $T_A=25^\circ\text{C}$ )	$P_D$	1.4	W
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JC}$	10	$^\circ\text{C/W}$
Thermal Resistance	$\theta_{JA}$	89.3	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=40\text{V}$		100	nA
$I_{CBO}$	$V_{CB}=40\text{V}, T_C=125^\circ\text{C}$		100	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=8.0\text{V}$		100	nA
$BV_{CEO}$	$I_C=10\text{mA}$	25		V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$		0.75	V
$V_{CE(SAT)}$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		1.8	V
$V_{BE(SAT)}$	$I_C=5.0\text{A}, I_B=1.0\text{A}$		2.5	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=2.0\text{A}$		1.6	V
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	70		
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=2.0\text{A}$	45	180	
$h_{FE}$	$V_{CE}=2.0\text{V}, I_C=5.0\text{A}$	10		
$f_T$	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=10\text{MHz}$	65		MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=0.1\text{MHz}$ (CJD200)		80	pF
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=0.1\text{MHz}$ (CJD210)		120	pF

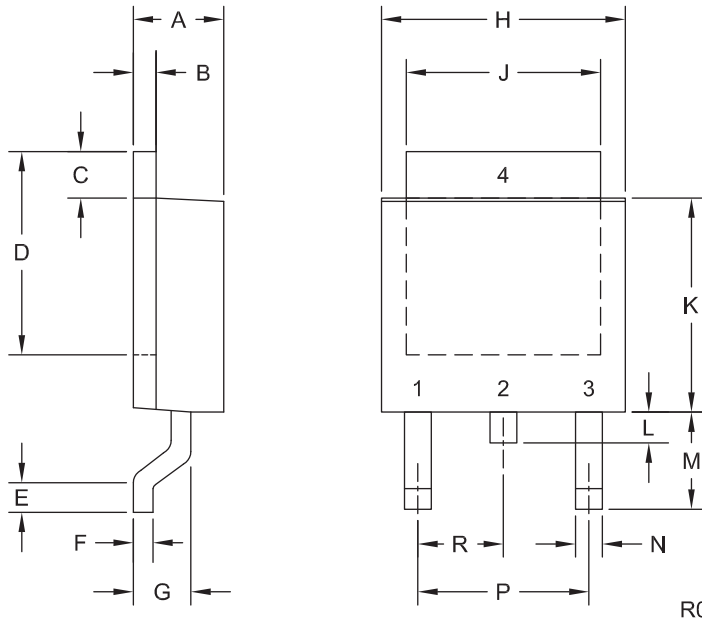
R3 (21-January 2013)

CJD200 NPN  
CJD210 PNP

SURFACE MOUNT SILICON  
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DPAK CASE - MECHANICAL OUTLINE



**LEAD CODE:**

- 1) Base
- 2) Collector
- 3) Emitter
- 4) Collector

**MARKING:**

FULL PART NUMBER

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.083	0.108	2.10	2.75
B	0.016	0.032	0.40	0.81
C	0.035	0.063	0.89	1.60
D	0.203	0.228	5.15	5.79
E	0.020	-	0.51	-
F	0.018	0.024	0.45	0.60
G	0.051	0.071	1.30	1.80
H	0.248	0.268	6.30	6.81
J	0.197	0.217	5.00	5.50
K	0.209	0.245	5.30	6.22
L	0.025	0.040	0.64	1.02
M	0.090	0.115	2.30	2.91
N	0.012	0.045	0.30	1.14
P	0.180		4.60	
R	0.090		2.30	

DPAK (REV: R0)

R3 (21-January 2013)